



## ZXTP56020FDBQ

#### 20V DUAL PNP LOW V<sub>CE(SAT)</sub> TRANSISTOR

#### Features

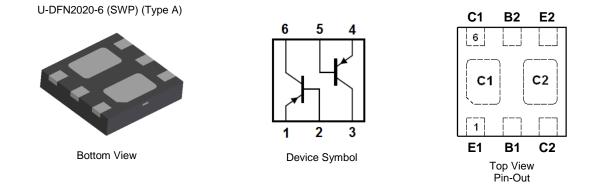
- BV<sub>CEO</sub> > -20V
- I<sub>C</sub> = -2A High Continuous Collector Current
- $R_{CE(SAT)} = 100m\Omega$  for a Low Equivalent On-Resistance
- Low Saturation Voltage V<sub>CE(SAT)</sub> < -150mV @ -1A</li>
- Sidewall Tin Plating for Wettable Flanks in AOI
- P<sub>D</sub> up to 2.47W for Power Demanding Applications
- Low Profile 0.6mm High Package for Thin Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

## Application

- Matrix LED Lighting
- Power Management

## Mechanical Data

- Case: U-DFN2020-6 (SWP) (Type A) with Sidewall Plating (SWP)
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin, Solderable per MIL-STD-202, Method 208 3
- Weight: 0.0065 grams (Approximate)



## Ordering Information (Notes 4 & 5)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXTP56020FDBQ-7	1W9	7	8	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

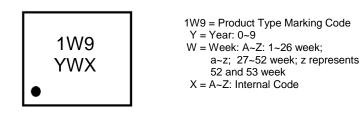
Notes:

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product\_compliance\_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**





## Absolute Maximum Ratings – Q1 & Q2 (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-20	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-20	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	lc	-2	А
Peak Pulse Collector Current	I <sub>CM</sub>	-3	A
Base Current	IB	-300	mA
Peak Base Current	I <sub>BM</sub>	-1	A

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Notes 6 & 8)		405	mW	
Power Dissipation	(Notes 6 & 9)	D	510		
rower Dissipation	(Notes 7 & 8)	PD	1650	TTIVV	
	(Notes 7 & 9)		2470		
	(Notes 6 & 8)		308		
Thermal Desistance Junction to Ambient	(Notes 6 & 9)	D	245	°C/W	
Thermal Resistance, Junction to Ambient	(Notes 7 & 8)	$R_{ heta}$ JA	76		
	(Notes 7 & 9)		51		
Thermal Resistance, Junction to Lead	(Note 10)	$R_{\theta JL}$	18	°C/W	
Operating and Storage Temperature Range	—	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

#### ESD Ratings (Note 11)

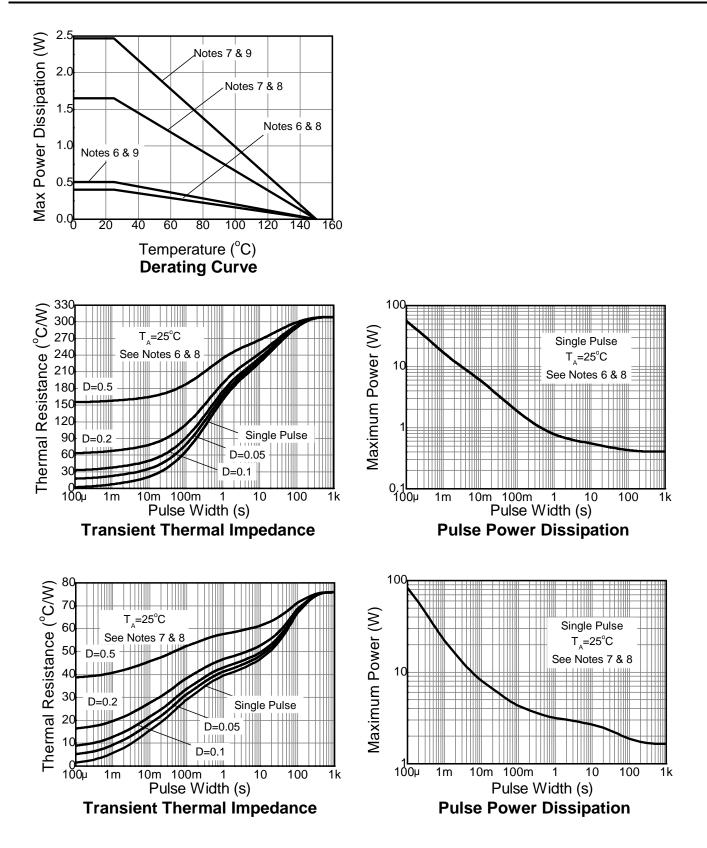
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

Notes: 6. For a device mounted with the exposed collector pads on minimum recommended pad layout that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state. 7. Same as note (6), except the device is mounted with the collector pad on 28mm x 28mm (8cm<sup>2</sup>) 2oz copper. 8. For a dual device with one active die.

9. For dual device with 2 active die running at equal power.
10. Thermal resistance from junction to solder-point (on the exposed collector pads).
11. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## Thermal Characteristics and Derating Information





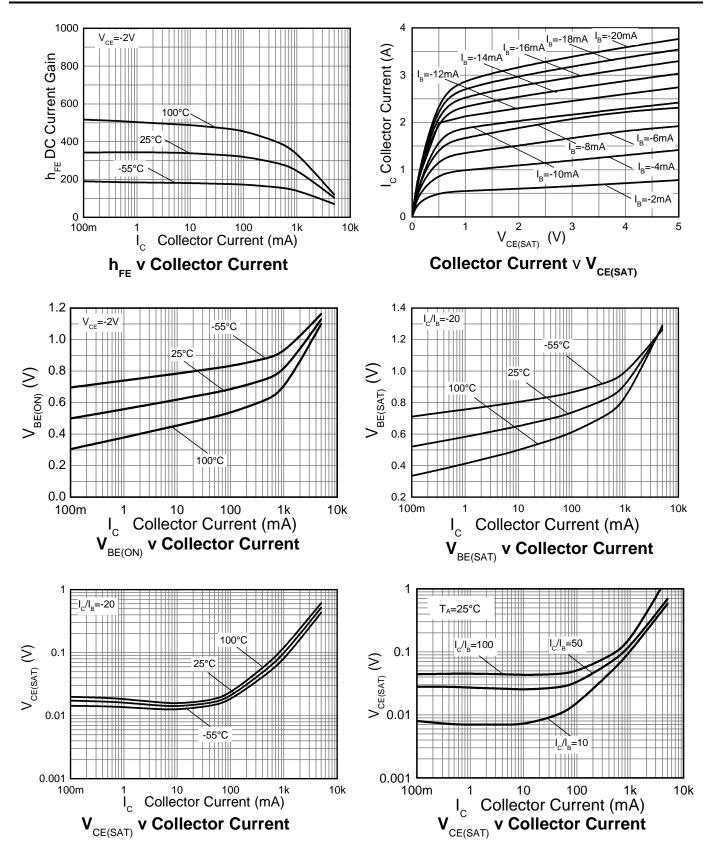
## Electrical Characteristics – Q1 & Q2 (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Мах	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-20		max	V	$I_{\rm C} = -100\mu A$
Collector-Emitter Breakdown Voltage (Note 12)	BVCBO	-20			v	$I_{\rm C} = -100\mu$ A
Emitter-Base Breakdown Voltage	BVCEO BVEBO	-7			v	$I_{\rm F} = -100\mu A$
	DAEBO	-		-100	nA	
Collector-Base Cutoff Current	I <sub>CBO</sub>			-100	μA	$V_{CB} = -16V, I_E = 0$
						$V_{CB} = -16V, I_E = 0, T_A = +150^{\circ}C$
Emitter-Base Cutoff Current	I <sub>EBO</sub>			-100	nA	$V_{EB} = -5.6V, I_{C} = 0$
		250		—		$V_{CE} = -2V, I_{C} = -100mA$
		210	—	—		$V_{CE} = -2V, I_C = -500mA$
DC Current Gain (Note 12)	h <sub>FE</sub>	170			—	$V_{CE} = -2V, I_{C} = -700mA$
		160				$V_{CE} = -2V, I_{C} = -1A$
		100				$V_{CE} = -2V, I_{C} = -2A$
	Vce(sat)			-110		$I_{\rm C} = -500$ mA, $I_{\rm B} = -50$ mA
		_		-220	mV	$I_{\rm C} = -1A, I_{\rm B} = -50 {\rm mA}$
Collector-Emitter Saturation Voltage (Note 12)		_	_	-200		I <sub>C</sub> = -0.7A, I <sub>B</sub> = -7mA
		_	_	-390		I <sub>C</sub> = -2A, I <sub>B</sub> = -200mA
Equivalent On-Resistance (Note 12)	R <sub>CE(SAT)</sub>	_		220	mΩ	$I_E = -1A, I_B = -50mA$
	V <sub>BE(SAT)</sub>	_	_	-1	V	I <sub>C</sub> = -0.5A, I <sub>B</sub> = -50mA
Base-Emitter Saturation Voltage (Note 12)		_		-1.1		I <sub>C</sub> = -1A, I <sub>B</sub> = -50mA
		_		-1.25		$I_{C} = -2A, I_{B} = -200 \text{mA}$
Base-Emitter Turn-on Voltage (Note 12)	V <sub>BE(ON)</sub>			-0.9	V	$V_{CE} = -2V, I_{C} = -0.5A$
Turn-On Time	t <sub>ON</sub>	_	60		ns	
Delay Time	t <sub>D</sub>	t <sub>D</sub> — 10			ns	$I_{C} = -1A, I_{B1} = -I_{B2} = 50mA;$
Rise Time	t <sub>R</sub>	_	50		ns	T <sub>A</sub> = +25°C

Note: 12. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

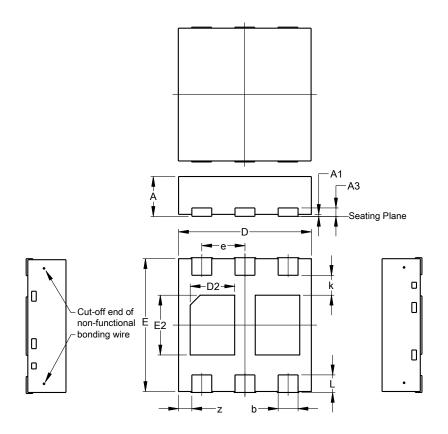




### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2020-6 (SWP) (Type A)

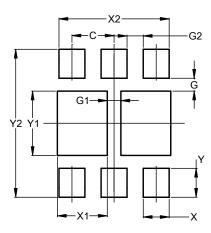


U-DFN2020-6 (SWP)						
	(Type A)					
Dim	Min	Max	Тур			
Α	0.55	0.65	0.60			
A1	0.00	0.05	0.03			
A3			0.127			
b	0.25	0.35	0.30			
D	1.95	2.05	2.00			
D2	0.57	0.77	0.67			
E	1.95	2.05	2.00			
E2	0.80	1.00	0.90			
е	0.65BSC					
k	0.30BSC					
L	0.22	0.32	0.27			
z	z 0.20BSC					
All	All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2020-6 (SWP) (Type A)



Dimensions	Value (in mm)
С	0.650
G	0.200
G1	0.210
G2	0.250
Х	0.400
X1	0.770
X2	1.700
Y	0.450
Y1	1.000
Y2	2.300



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